

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Filed Named John P. Snyder
Inventor:

Application No.: 10/796,514

Filing Date: 03/09/2004

Title: TRANSISTOR HAVING HIGH DIELECTRIC
GATE INSULATING LAYER AND SOURCE
AND DRAIN FORMING SCHOTTKY
CONTACT WITH SUBSTRATE

Confirmation No.: 1961

Examiner: Kim, Su C

Group Art Unit: 2823

RESPONSE AFTER FINAL UNDER 37 C.F.R. 1.116

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22313-1450 on this 13 day of November 2007.

Dmitry
(Signature)

Dear Sir:

Applicant hereby submits a response to the Final Office Action dated June 11, 2007.

Claims are reflected in the listing of claims which begins on page 2 of this paper. Claims 1, 15, 24, 33, 44 and 55 have been amended to patentably distinguish the present invention over the cited prior art.

Remarks/Arguments begin on page 11 of this paper.

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